

**AMENDMENTS TO THE CLAIMS**

1. (Currently Amended) A liquid crystal display (LCD) device, comprising:  
a thin film transistor (TFT) formed on a substrate, the TFT having a gate, a source and a drain;  
a color filter layer on the TFT, and in direct contact with the source and the drain, wherein said contact is only at a portion where said color filter layer is overlapping only edge portions of the source and drain so as to prevent light leakage and improve an aperture ratio; [[and]]

a planarization layer formed over the TFT and the color filter layer, and  
a pixel electrode formed above the planarization layer and the color filter layer to be in electrical contact with the drain through a contact hole formed in the planarization layer where the color filter layer is not formed.

2. (Currently Amended) The device of claim 1, wherein the color filter layer and [[e]] the drain are in direct contact such that there are no intermediaries therebetween.

3. (Previously Presented) A method of manufacturing a liquid crystal display (LCD) device, comprising:

forming a thin film transistor (TFT) on a substrate, the TFT having a gate, a source and a drain;

forming a color filter layer on the TFT, in direct electrical contact with the source and the drain, wherein said electrical contact is only at a portion where said color filter layer is overlapping only edge portions of the source and drain so as to prevent light leakage and improve an aperture ratio; [[and]]

forming a planarization layer over the TFT and the color filter layer; and

forming a pixel electrode above the planarization layer and the color filter layer to be in electrical contact with the drain through a contact hole formed in the planarization layer where the color filter layer is not formed.

4. (Previously Presented) The method according to claim 3, wherein the LCD is manufactured without forming a passivation layer between the TFT and the color filter layer.

5. (New) The device of claim 1, wherein the planarization layer is formed from SiO<sub>x</sub>, SiN<sub>x</sub> or benzocyclobutene.

6. (New) The method of claim 1, wherein the planarization layer is formed from SiO<sub>x</sub>, SiN<sub>x</sub> or benzocyclobutene.

7. (New) The device of claim 1, wherein the pixel electrode is formed from indium tin oxide.

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8. (New) The method of claim 1, wherein the pixel electrode is formed from indium tin oxide.